

Docket No. 740756-2297

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)
Shunpei YAMAZAKI et al.) Group Art Unit: 2814
Serial No. 09/837,558) Examiner: Ngan V. Ngo
Filed: April 19, 2001)
For: SEMICONDUCTOR DEVICE AND) Date: September 20, 2002
MANUFACTURING METHOD THEREOF)

RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Official Action of August 26, 2002, Applicants respond as follows:

IN THE CLAIMS:

Please cancel claims 17-30 without prejudice or disclaimer to file a divisional application directed thereto.

Please add new claims 33-50 as follows:

- 33. A method of manufacturing a semiconductor device comprising:
- forming a conductive film over a substrate;
 - patterning said conductive film to form at least one first wiring, said first wiring including at least one first gate electrode;
 - forming a first insulating film over said first wiring and said substrate;
 - forming a first semiconductor island and a second semiconductor island wherein said first semiconductor island is located over said first gate electrode with said first insulating film

NVA240673.1